

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Applicant: Francis Yu-Hei Tsang et al.  
Title: NUCLEAR VOLTAIC CELL

Docket No.: 2408.001US1  
Filed: November 21, 2003  
Examiner: Unknown

Serial No.: 10/720,035  
Group Art Unit: 3663


**Mail Stop Amendment**  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

We are transmitting herewith the following attached items (as indicated with an "X"):

- ☒ Communication Concerning Related Applications (1 pg.).
- ☒ Information Disclosure Statement (2 pgs.), Form 1449 (4 pgs.), and copies of 53 cited documents.

Please charge any additional fees or credit overpayment to Deposit Account No. 19-0743.

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.  
Customer Number 21186

By   
Atty: Steven R. Gilliam  
Reg. No. 51,734

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SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.  
(GENERAL)

S/N 10/720,035

PATENT

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COMMUNICATION CONCERNING RELATED APPLICATIONS

**Mail Stop Amendment**

Commissioner for Patents

P.O. Box 1450

Alexandria, VA 22313-1450

Applicants would like to bring to the Examiner's attention the following related applications in the above-identified patent application:

<u>Serial/Patent No.</u>	<u>Filing Date/Issue Date</u>	<u>Attorney Docket</u>	<u>Title</u>
11/214,079	August 29, 2005	2408.001US2	NUCLEAR VOLTAIC CELL
11/214,078	August 29, 2005	2408.001US3	NUCLEAR VOLTAIC CELL
11/214,280	August 29, 2005	2408.001US4	NUCLEAR VOLTAIC CELL

Continuations and divisionals may be later filed on the cases listed above, or cited to the Examiner in any previous Communication Concerning Related Applications. Applicants request that the Examiner review all continuations and divisionals of the above-listed or previously-cited patent applications before allowing the claims of the present patent application.

Respectfully submitted,  
FRANCIS Y. TSANG ET AL.

By Applicants' Representatives,  
SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.  
P.O. Box 2938  
Minneapolis, MN 55402  
512.492.6406

Date 11-Jan-2007

By

  
Steven R. Gilliam  
Reg. No. 51,734

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Steven R. Gilliam  
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Signature

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:	Francis Yu-Hei Tsang et al.	Examiner:	Unknown
Serial No.:	10/720,035	Group Art Unit:	3663
Filed:	November 21, 2003	Docket:	2408.001US1
Title:	NUCLEAR VOLTAIC CELL		

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INFORMATION DISCLOSURE STATEMENT

Mail Stop Amendment  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

In compliance with the duty imposed by 37 C.F.R. § 1.56, and in accordance with 37 C.F.R. §§ 1.97 *et. seq.*, the enclosed materials are brought to the attention of the Examiner for consideration in connection with the above-identified patent application. Applicants respectfully request that this Information Disclosure Statement be entered and the documents listed on the attached Form 1449 be considered by the Examiner and made of record. Pursuant to the provisions of MPEP 609, Applicants request that a copy of the 1449 form, initialed as being considered by the Examiner, be returned to the Applicants with the next official communication.

Pursuant to 37 C.F.R. §1.97(b), it is believed that no fee or statement is required with the Information Disclosure Statement. However, if an Office Action on the merits has been mailed, the Commissioner is hereby authorized to charge the required fees to Deposit Account No. 19-0743 in order to have this Information Disclosure Statement considered.

Pursuant to 37 C.F.R. 1.98(a)(2), Applicant believes that copies of cited U.S. Patents and Published Applications, and Non-Published Applications identifiable by USPTO Serial Number, are no longer required to be provided to the Office. Notification of this change to this effect was provided in the United States Patent and Trademark Office OG Notices dated October 12, 2004 and October 19, 2004. Thus, Applicant has not included copies of any US Patents or US Patent Applications identifiable by serial number that may be cited with this submission. Should the Office require copies to be provided, Applicant respectfully requests that notice of such requirement be directed to Applicant's below-signed representative. Applicant acknowledges the requirement to submit copies of foreign patent documents and non-patent literature in accordance with 37 C.F.R. 1.98(a)(2).

The Examiner is invited to contact the Applicants' Representative at the below-listed telephone number if there are any questions regarding this communication.

Respectfully submitted,  
FRANCIS YU-HEI TSANG ET AL.

By their Representatives,  
SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.  
P.O. Box 2938  
Minneapolis, MN 55402  
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11 day of January 2007.

Steven R. Gilliam  
Name

  
Signature

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PTO FORM 1449A-PTO (10/01/2000) GSA GEN. REG. NO. 27  
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Complete if Known	
Application Number	10/720,035
Filing Date	November 21, 2003
First Named Inventor	Tsang, Francis
Group Art Unit	3663
Examiner Name	Unknown
Attorney Docket No: 2408.001US1	

Sheet 1 of 4

**US PATENT DOCUMENTS**

Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Filing Date If Appropriate
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Examiner Initial *	Cite No	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	1*
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EXAMINER

DATE CONSIDERED

Substitute Disclosure Statement Form (PTO-1449)

\* EXAMINER Initial: If reference considered, whether or not citation is in accordance with MPEP § 809. (Draw line through citation if not in accordance and not considered). Include copy of this form with next communication to applicant. Applicant's unique citation designation number (optional). Applicant is to place a check mark here if English language Translation is attached.

**INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT**  
(Use as many sheets as necessary)

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Application Number	10/720,035
Filing Date	November 21, 2003
First Named Inventor	Tsang, Francis
Group Art Unit	3663
Examiner Name	Unknown
Attorney Docket No: 2408.001US1	

Sheet 2 of 4

**OTHER DOCUMENTS – NON PATENT LITERATURE DOCUMENTS**

Examiner Initials*	Cite No	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T
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**INFORMATION DISCLOSURE  
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<b>Application Number</b>	10/720,035
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<b>Group Art Unit</b>	3663
<b>Examiner Name</b>	Unknown

Sheet 4 of 4

Attorney Docket No: 2408.001US1

**OTHER DOCUMENTS – NON PATENT LITERATURE DOCUMENTS**

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EXAMINER

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Substitute Disclosure Statement Form (PTO-1446)

\* EXAMINER: Initial if reference considered, whether or not contained in conference with NPTP 850. Draw line through (initials) if not in conference and not considered. Include copy of this form with mail communication to applicant. Applicant's unique citation designation number (initials) &gt; Applicant is to place a check mark here if English language translation is attached.